

ABSTRACT OF THE DISCLOSURE

A method is described for manufacturing electronic semiconductor devices comprising the steps of depositing in sequence a layer of hydrophobic material and a "deep UV" photo-resist layer on a semiconductor substrate, selectively removing the "deep UV" photo-resist layer and hydrophobic material in order to expose definite portions of the semiconductor substrate and etch the exposed portions by means of an watery acid solution. This method allows semiconductor devices to be manufactured, also having very critical sizes and with a convenient resolution and control of circuit patterns formed thereon through etching with watery acid solutions.

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